

### 12500 TI Boulevard, MS 8640, Dallas, Texas 75243

# PCN# 20180509001.1 PO Thickness change on the LBC7 process node Change Notification / Sample Request

**Date:** May 18, 2018

To: TOKYO ELECTRON DEVICE (DSTR) PCN

#### Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

We request you acknowledge receipt of this notification within **30** days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If you require samples or additional data to support your evaluation, please request within 30 days.

The changes discussed within this PCN will not take effect any earlier than **90** days from the date of this notification, unless customer agreement has been reached on an earlier implementation of the change. This notification period is per TI's standard process.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice, contact your local Field Sales Representative or the PCN Manager (PCN www admin team@list.ti.com).

PCN Team SC Business Services

## 20180509001.1 Attachment: 1

## **Products Affected:**

The devices listed on this page are a subset of the complete list of affected devices. According to our records, these are the devices that you have purchased within the past twenty-four (24) months. The corresponding customer part number is also listed, if available.

DEVICE	<b>CUSTOMER PART NUMBER</b>
TPS562201DDCR	null
TPS563201DDCR	null
TPS562201DDCT	null
TPS562208DDCR	null
TPS563208DDCR	null
TPS7A9101DSKT	null
TPS7A9001DSKT	null
TPS563201DDCT	null

Technical details of this Product Change follow on the next page(s).

PCN Num	ber:	2018	20180509001.1				PCN Date:		:	May 18, 2018
Title:	Title: LBC7 change total PO thickness from 24kA to 39kA									
Customer	Contact:		PCN Manager				Dept:			Quality Services
Proposed	1 <sup>st</sup> Ship Date	:	Aug 18, 2018			Estimated Sample Availability:		le	Date provided at sample request.	
Change T	уре:									
Assem	nbly Site		Assembly Process				Assembly Materials			
Desig			<u> </u>	Electrical Spec						chanical Specification
Test S			<u> </u>	Packing/Shipp				Щ		st Process
	Bump Site		<u> </u>	Wafer Bump M						ifer Bump Process
water	Fab Site		<u>H</u>	Wafer Fab Mat				$\boxtimes$	wa	ifer Fab Process
				Part number c						
Description	on of Change:			PCN D	<del>'e</del> la	1115				
This change notification is to announce a total PO Thickness change from 24kA to 39kA by increasing the 2 <sup>nd</sup> Oxide Teos thickness from 3kA to 18kA on the LBC7 process node for the selected devices listed in the "Product Affected" section.										
	Change From Change To						То			
13kA HDP Oxide + 3kA Teos Oxide + 8kA Nitride passivation			1	13kA HDP Oxide + 18kA Teos Oxide + 8kA Nitride passivation						
Qual details are provided in the Qual Data Section.										
Reason for Change:										
Continuity	of supply.									
Anticipate	ed impact on	Form,	, Fit	, Function, Qu	alit	y or Rel	iability	/ (p	osit	ive / negative):
None										
Changes to product identification resulting from this PCN:										
None										
Product Affected:										
TPS53605I	DSQT	TPS56	5220	8DDCT	TPS:	563208D	DCR		TP	S7A9101DSKT
TPS56220:	1DDCR	TPS56	63201DDCR TF			7A9001D	SKR		TP	S7A9201DSKR
TPS56220:	1DDCT	TPS56	63201DDCT T			7A9001D	001DSKT			S7A9201DSKT
TPS562208						7A9101D				
	<u>'</u>			<u> </u>						

# **Qualification Report**

### LBC7 - Thick TEOS at PO 2nd OX DEP

## Approve Date 9-April-2018

### **Product Attributes**

Attributes	Qual Device: TP\$563201DDCR
Assembly Site	JCET
Package Family	SOT-23-T
Wafer Fab Supplier	RFAB
Wafer Process	LBC7
Flammability Rating	UL 94 V-0

<sup>-</sup> Qual Devices qualified at LEVEL1-NACG: Devices TPS563201DDCR

#### **Qualification Results**

Data Displayed as: Number of lots / Total sample size / Total failed

Type	Test Name / Condition	Duration	Qual Device: TPS563201DDCR
HAST	Biased HAST, 130C/85%RH	192 Hours	3/231/0
HTSL	High Temp. StorageBake, 170C	420 Hours	3/231/0
MQ	Manufacturability (Assembly)	(per mfg. Site specification)	3/Pass
TC	Temperature Cycle, -65/150C	750 Cycles	3/231/0

<sup>-</sup> Preconditioning was performed for Auto clave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com